



PAPER

Indium doping effects on the structural, morphological and electrical properties of WO₃ powder pelletsRECEIVED
5 September 2024REVISED
18 December 2024ACCEPTED FOR PUBLICATION
13 January 2025PUBLISHED
30 January 2025Najla M Khusayfan¹, Hazem K Khanfar²  and Seham R Alharbi¹¹ Department of Physics, Faculty of Science, University of Jeddah, Jeddah, Saudi Arabia² Department of Computer Systems Engineering, Arab American University, Palestine[†][†] Publisher's note. Whilst IOP Publishing adheres to and respects UN resolutions regarding the designations of territories (available at <http://www.un.org/press/en>), the policy of IOP Publishing is to use the affiliations provided by its authors on its published articles.E-mail: Hazem.Khanfar@aaup.eduKeywords: WO₃ powders, indium doping, structural parameters, quad band, 5 G/6 G applications**Abstract**

Tungsten oxide powders were doped with indium at weight percentages ranging from 5 to 15 wt% and pressed into pellet form under a pressure of 200 bars. The doping process was carried out using the solid-state reaction technique. The doped samples were sintered at 750 °C for 12 h. Both undoped and indium-doped powder pellets exhibited a triclinic structure, with hexagonal In_xWO₃ emerging as a minor phase that increased with higher indium content. Indium doping increased microstrain, the percentage of stacking faults, and defect concentration while decreasing the crystallite sizes in the WO₃ powder pellets. Morphological analysis of the samples revealed irregular grain shapes and sizes within the pellets. Notably, indium doping significantly reduced the porosity of WO₃ from 7.42% to 3.83% as the indium content increased to 15 wt%. Electrically, the n-type resistivity increased with higher doping levels, indicating deeper donor levels. Specifically, the donor states in the powder pellets increased from 0.21 eV to 0.27 eV as the indium content rose from 5 wt% to 10 wt%, and further reached 0.29 eV at 15 wt% indium. Moreover, AC signal analysis of the powder pellets demonstrated their potential as microwave resonators suitable for antenna applications. Indium doping effectively engineered the maximum cutoff frequency, with values reaching 80 GHz in WO₃ pellets doped with 15 wt% indium. These powder pellets, with thicknesses not exceeding 700 μm and electrode areas of 3.14 × 10⁻² cm², show great promise for 5 G/6 G technology applications as concurrent quad-band antennas.

1. Introduction

Tungsten oxide has gained a wide space in literature due to its novel applications. The material is used for the fabrication of supercapacitors [1], flexible electrochromic devices [2], gas sensors [3] and terahertz dielectric lenses [4]. As supercapacitors nickel doped WO₃ fabricated by the sol-gel technique displayed maximum specific capacitance of 279 F g⁻¹ proofing their potential for energy storage applications [1]. As electrochromic devices WO₃ thin films showed high coloration efficiency in the visible and near infrared regions [2]. Such features of the device nominate them as smart windows to control the light and heat fluxes as well [2]. In addition, nanostructured WO₃ gas-sensors showed high sensitivity for nickel oxide, ammonia gases and volatile organic compounds [3]. Moreover, WO₃ films coated with Fe nanosheets were found ideal as dielectric lenses. These lenses exhibited cutoff frequency in the range of 1.0–30.0 THz in addition to their enhanced light absorbability [4].

Vareous techniques are employed to enhance the performance of WO₃ nanoparticles (powders) to make them stabler and adequate for technological applications. As for examples, 7.5 at% lanthanum doping into WO₃ nanoparticles enhanced their NiO₂, NH₃, SO₂, CO, CO₂ and CH₄ gas sensitivity [5]. The doping improved the resistance of the powders to the humidity fluctuations [5]. In addition, indium doped WO₃ cubic nano-blocks synthesized via one-pot hydrothermal method exhibited high repeatability, long term stability and high